

# Rochester Electronics Manufactured Components

Rochester branded components are manufactured using either die/wafers purchased from the original suppliers or Rochester wafers recreated from the original IP. All recreations are done with the approval of the OCM.

Parts are tested using original factory test programs or Rochester developed test solutions to guarantee product meets or exceed the OCM data sheet.

### **Quality Overview**

- ISO-9001
- AS9120 certification
- Qualified Manufacturers List (QML) MIL-PRF-35835
  - Class Q Military
  - Class V Space Level
- Qualified Suppliers List of Distributors (QSLD)
- Rochester is a critical supplier to DLA and meets all industry and DLA standards.

Rochester Electronics, LLC is committed to supplying products that satisfy customer expectations for quality and are equal to those originally supplied by industry manufacturers.

The original manufacturer's datasheet accompanying this document reflects the performance and specifications of the Rochester manufactured version of this device. Rochester Electronics guarantees the performance of its semiconductor products to the original OEM specifications. 'Typical' values are for reference purposes only. Certain minimum or maximum ratings may be based on product characterization, design, simulation, or sample testing.



# Monolithic JFET-Input Operational Amplifiers

# PM-155A/PM-156A/PM-157A

### **FEATURES**

### **All Devices**

- Low Input Bias and Offset Currents
- Low Input Offset Voltage ...... 1.0mV
- Low Input Offset Voltage Drift · . . . . . . . . 3.0 μV/° C
- Low Input Noise Current ........... 0.01pA/√Hz
   Use Common Made Polestian Potts
   100dB
- High Common-Mode Rejection Ratio . . . . . . . . . 100dB

PM-155 (Only) ..... LF155 Replacement Low-Supply Current ..... 2mA

PM-157 (Only) ..... LF157 Replacement

Wide-Bandwidth Decompensated (AvcL = 5 Min) ... 20MHz
High Siew Rate

45V/µsec

High Siew Rate
 Fast Settling to ±0.01%
 45V/μsec
 4.0μsec

### **GENERAL DESCRIPTION**

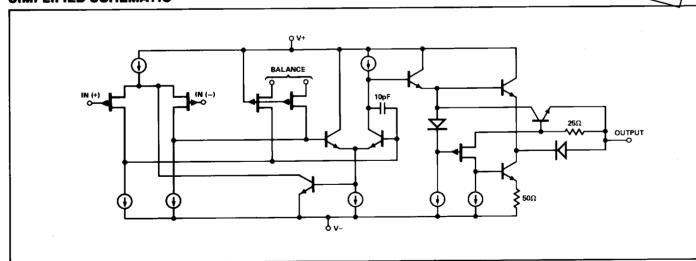
The PM JFET-input series provides low input current, high slew rate, and direct interchangeability with LF155, 156, and 157 types. These operational amplifiers use a new process which allows fabrication of matched JFET transistors and standard bipolar transistors on the same chip. High accuracy and low cost make the PM JFET-input series useful in new designs and as replacements for modular and hybrid types. Unlike many designs, nulling the input offset voltage does not degrade common-mode rejection ratio or input offset voltage drift. Low input voltage noise and current noise plus a low 1/f noise corner frequency allow these amplifiers to be used in a variety of low noise, wide-bandwidth applications.

Dynamic specifications for the PM-155 include a slew rate of  $5V/\mu s$ , a 2.5MHz gain bandwidth product, and settling time to within  $\pm 0.01\%$  of final value in  $5.0\mu s$ . The PM-156 has a slew rate of  $12V/\mu s$  and a settling time of  $4.0\mu s$  to  $\pm 0.01\%$  of final value.

The PM-157 is a very last decompensated device. This results in a 45V/µs slew rate, a 20MHz gain bandwidth product, and a settling time of 4.0µs. Decompensation/requires a minimum closed-loop gain of five because of stability considerations.

For improved performance, see the OP-15/OP-16/OP-17 data sheet. For duals, see the OP-215 data sheet.

### SIMPLIFIED SCHEMATIC



### **ABSOLUTE MAXIMUM RATINGS**

Supply Voltage
PM-155A, PM-156A, PM-157A, PM-155, PM-156, PM-157,
PM-355A, PM-356A, PM-357A ±22V
Operating Temperature Range
PM-155A, PM-156A, PM-157A, PM-155, PM-156,
PM-15755° C to +125° C
PM-355A, PM-356A, PM-357A 0°C to +70°C
Maximum_Junction Temperature (Tj)
PM-155A, PM-156A, PM-157A, PM-155, PM-156,
PM-157+150°C
PM-355A, PM-356A, PM-357A+100°C
Differential Input Voltage
PM-155A, PM-156A, PM-157A, PM-155, PM-156, PM-157,
PM-355A, PM-356A, PM-357A ±40V
Input Voltage
PM-155A, PM-156A, PM-157A, PM-155, PM-156, PM-157,
PM-355A, PM-356A, PM-357A ±20V

Output Short-Circuit Duration	Indefinite
Storage Temperature Range	65°C to +150°C
Lead Temperature Range (Soldering, 60	

PACKAGE TYPE	Θ <sub>jA</sub> (NOTE 2)	Θ <sub>IC</sub>	UNITS
TO-99 (J)	150	18	°C/W
8-Pin Hermetic DIP (Z)	148	16	°C/W
20-Contact LCC (RC)	98	38	°C/W

#### NOTES:

- The absolute maximum negative input voltage is equal to the negative power supply voltage.
- Θ<sub>jA</sub> is specified for worst case mounting conditions, i.e., Θ<sub>jA</sub> is specified for device in socket for TO, CerDIP, and LCC packages.

**ELECTRICAL CHARACTERISTICS** at  $\pm 15 \text{V} \leq \text{V}_S \leq \pm 20 \text{V}$ ,  $-55^{\circ}\text{C} \leq \text{T}_A \leq +125^{\circ}\text{C}$  and  $\text{T}_{HIGH} = +125^{\circ}\text{C}$  for PM-155A, PM-156A and PM-157A,  $0^{\circ}\text{C} \leq \text{T}_A \leq +10^{\circ}\text{C}$  and  $\text{T}_{HIGH} = +70^{\circ}\text{C}$  for PM-355A, PM-356A and PM-357A, unless otherwise noted.

PARAMETER	SYMBOL	SONDITIONS	\\/ <i> </i> F	PM-155. PM-156. PM-157. TYP	N _	P	M-355 M-356 M-357	A/	UNITS
Input Offset Voltage	Vos	$R_S = 50\Omega$	/ [ ] -	1.4	2.5		4.2	2.3	7 mV
Input Offset Voltage Drift	TCVos	R <sub>S</sub> = 50Ω	/	3	<b> </b>	<u> </u>	*	5	
Change in Input Offset Drift with V <sub>OS</sub> Adjust	$\left(\frac{\Delta TCV_{OS}}{\Delta V_{OS}}\right)$	$R_S = 50\Omega$		<b>3</b> .5			9.5	<u> </u>	μV/° C per mV
Input Offset Current	los	T <sub>j</sub> ≤ T <sub>HIGH</sub> (Note 1)		4.0	10	<u> </u>	0.4	1.0	- RA
Input Bias Current	I <sub>B</sub>	T <sub>j</sub> ≤ T <sub>HIGH</sub> (Note 1)		±10	±25		±2	±5_/	nA
Large-Signal Voltage Gain	A <sub>VO</sub>	$V_S = \pm 15V, V_O = \pm 10V,$ $R_L = 2k\Omega$	25	75	_	25	75		V/mV
Output Voltage Swing	v <sub>o</sub>	$V_S = \pm 15V$ , $R_L = 10k\Omega$ $V_S = \pm 15V$ , $R_L = 2k\Omega$	±12 ±10	±13 ±12	_	±12 ±10	±13 ±12	_	v
Input Voltage Range	IVR	V <sub>S</sub> = ± 15V	± 10.4	+15.1 -12.0	_	±10.4	+15.1 -12.0	_	v
Common-Mode Rejection Ratio	CMRR	V <sub>CM</sub> = ±IVR	85	100	<del>-</del>	85	100	_	dB
Power Supply Rejection Ratio	PSRR	(Note 2)	_	10	57	_	10	57	μV/V

#### MOTES

- 1. PMI has a bias current compensation circuit which gives improved bias current over the standard JFET input op amps.  $I_B$  and  $I_{OS}$  are measured at  $V_{CM} = 0$ .
- Power supply rejection ratio is measured for both supply magnitudes increasing or decreasing simultaneously, in accordance with common practice.

### **ELECTRICAL CHARACTERISTICS** at $\pm$ 15V $\leq$ V<sub>S</sub> $\leq$ $\pm$ 20V, T<sub>A</sub> = 25° C, unless otherwise noted.

				PI	M-155 M-156 M-157	A/	Pi	M-355 M-356 M-357	A/	
PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	MIN	TYP	MAX	UNIT
Input Offset Voltage	Vos	R <sub>S</sub> = 50Ω		_	1	2	_	1	2	m
Input Offset Current	los	T <sub>j</sub> = 25° C (Note 1)		_	3	10	_	3	10	p.
Input Bias Current	l <sub>B</sub>	T <sub>j</sub> = 25° C (Note 1)		_	±30	±50		±30	±50	P
Input Resistance	RIN			_	10 <sup>12</sup>	_	_	10 <sup>12</sup>	_	
Large-Signal Voltage Gain	A <sub>vo</sub>	$V_S = \pm 15V$ , $V_O = \pm 10V$ , $R_L = 2k\Omega$		50	200	_	50	200	_	V/m
Supply Current	1	V <sub>S</sub> = ±15V	PM-155	_	2	4	_	2	4	
Supply Current	I <sub>SY</sub>	¥8-±10¥	PM-156/PM-157		5	7		5	7	m.
		A	PM-155	3	5	_	3	5	_	
Siew Rate	SR	$A_{VCL} = +1, V_S = \pm 15V$	PM-156	10	12	_	10	12	_	V/ <sub>4</sub>
$\bigcirc$		$A_{VCL} = +5, V_S = \pm 15V$	PM-157	40	45		40	45	_	
		A _ 14 W _ 44EW	PM-155	_	2.5	_	_	2.5		
Gain Bandyridth Product	GBW /	A <sub>VCL</sub> =+1, V <sub>S</sub> =±15V	PM-156	4.0	4.5		4.0	4.5	_	MH
	<u> </u>	AVCL = +5, V <sub>S</sub> = ±15V	PM-157	15	_ 20	-	15	20		
$\bigcirc$ / $\cap$	\		PM-155	_	5.0	_	_	4.0	_	
Settling Fime (to ± 0.01%)	) t <sub>s</sub> ) `	V <sub>S</sub> = ±15V (Note 2)	PM-156	_	4.0	_	_	1.5	_	
		Vs = ± 15V (Note 3)	PM-167 / /	_	4,0	_	_	1.5	_	
		Re=1000, f = 100Hz	1	_	25			25		
		$R_S = 100\Omega, f = 1000Hz$	/PM-1/55 / /	_	20 /		1 /	20	_	
Input Noise Voltage	en	$R_S = 100\Omega$ , $f = 100Hz$		_	/ 15/	`	<sup>1</sup>	15	<b>\</b>	nV/√Hz
		R <sub>S</sub> = 100Ω, f = 1008Hz	PM-156/PM-157	_	/ 12_		4	/12-	J	
,		f = 100Hz, V <sub>S</sub> = ±15V			0.01	<del></del>		0.01	-L	
Input Noise Current	in	$f = 1000 Hz, V_S = \pm 15V$		J_/	0.01	<u>_</u>	_	0.01	<u> </u>	pA/√H2
Input Capacitance	C <sub>IN</sub>	<del>_</del>			3	$\overline{}$	/-/	3	1-1	7p
NOTES:				-					T T	

- PMI has a bias current compensation circuit which gives improved bias current over the standard JFET input op amps. I<sub>B</sub> and I<sub>OS</sub> are measured at V<sub>CM</sub> = 0.
- Settling time is defined here for a unity gain inverter connection using 2kΩ
  resistors. It is the time required for the error voltage (the voltage at the
  inverting input pin on the amplifier) to settle to within 0.01% of its final
  value from the time a 10V step input is applied to the inverter. See settling
  time test circuit.
- 3. Settling time is defined here for a  $A_V = -5$  connection with  $R_F = 2k\Omega$ . It is the time required for the error voltage (the voltage at the inverting input pin on the amplifier) to settle to within 0.01% of its final value from the time a 2V step input is applied to the inverter. See settling time test circuit.

ELECTRICAL CHARACTERISTICS at ± 15V ≤ V<sub>S</sub> ≤ ± 20V and −55° C ≤ T<sub>A</sub> ≤ + 125° C and T<sub>HIGH</sub> = + 125° C for PM-155, PM-156

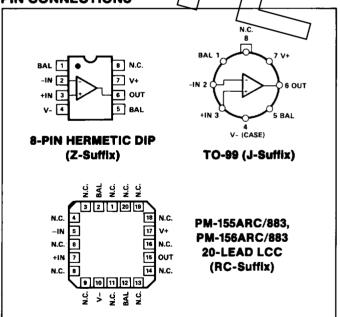
PARAMETE	:R	SYMBOI	L CONDIT	IONS		MIN	PM-155 PM-156 PM-157 TYP	MAX	UNITS
Input Offset	Voltage	Vos	R <sub>S</sub> = 50Ω		_		4	7	mV
nput_Offset Drift	Voltage	TCVos	R <sub>S</sub> = 50Ω			_	5	_	μV/° C
Change In I Drift With	nput Offset V <sub>OS</sub> Adjust.	$\left(\frac{\Delta TCV_{OS}}{\Delta V_{OS}}\right)$	່) R <sub>S</sub> = 50Ω	1		ज	0.5	_	μV/°C per mV
nput Offset	Current	los	T <sub>j</sub> ≤ T <sub>HIG</sub>	H (Note 1)		_	8	20	nA
nput Bias C	Current	IB	T <sub>j</sub> ≤ T <sub>HIG</sub>	H (Note 1)		_	±2	±50	nA
arge-Signa	il Voltage	A <sub>vo</sub>	$V_S = \pm 15$ $R_L = 2k\Omega$	$V, V_0 = \pm 10V$		25	75	_	V/mV
Oxtput Volt	age Swing		•	V, R <sub>L</sub> = 10k $\Omega$ V, R <sub>L</sub> = 2k $\Omega$		±12 ±10	± 13 ± 12	_	V
nput Voltag	e Range	JVR)	V <sub>S</sub> = ±15	v		±10.4	+15.1 -12.0	_	v
Common-M	<i>7</i>	CNIRR	V <sub>CM</sub> =±	VR	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	85	100	_	dB
ower Supp Rejection f		PSRR	(Note 2)		) / _/_			57	μV/V
current o	over the standar , T <sub>j</sub> = +125° C.	d JFET input op	circult which give amps. Igand los		ncreasi	ng or decreasing s	tio is meas	sured for usly, in/a	both supply magnitudes
ORDER	ING INFOR		;		PIN CO	NNECTIONS	<u> </u>		+
r <sub>A</sub> = 25°C V <sub>OS</sub> MAX (mV)	TO-99 8-PIN	8-PIN HERMETIC DIP	rcc	OPERATING TEMPERATURE RANGE		- <b></b>		BAL 1	N.C. 8 8 7 V+
2.0	PM155AJ* PM156AJ* PM157AJ/883	PM155AZ/883 PM156AZ* PM157AZ*	PM155ARC/883 PM156ARC/883	MIL	-18	8 N 7 V 3 + 6 0		-IN 2	<b>1</b> 00 € 00 T

PM356AZ СОМ 2.0 PM356AJ PM357AJ PM357AZ PM155J\* PM155Z\* 5.0 PM156J\* PM156Z\* MIL PM157J\* PM157Z\* For devices processed in total compliance to MIL-STD-883, add /883 after part

PM355AZ

PM355AJ

Burn-in is available on commercial and industrial temperature range parts in CerDIP, plastic DIP, and TO-can packages.



number. Consult factory for 883 data sheet.

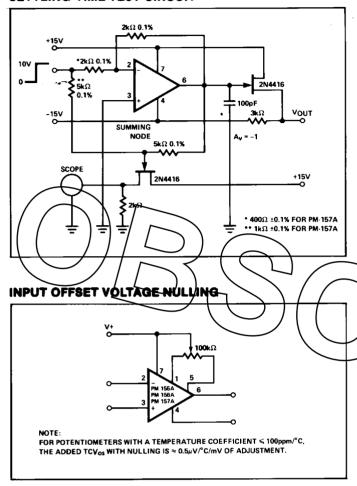
**ELECTRICAL CHARACTERISTICS** at  $T_A = +25^{\circ}$  C,  $\pm 15$  V  $\leq$  V<sub>S</sub>  $\leq \pm 20$  V for PM-155, PM-156 and PM-157, unless otherwise noted.

					PM-15: PM-15: PM-15	5	
PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS
Input Offset Voltage	Vos	R <sub>S</sub> =50Ω		_	3	5	mV
Input Offset Current	los	T <sub>j</sub> = 25° C (Note 1)		_	3	20	рА
Input Bias Current	I <sub>B</sub>	T <sub>j</sub> = 25° C (Note 1)			±30	±100	рА
Input Resistance	R <sub>IN</sub>	·		_	10 <sup>12</sup>	_	u
Large-Signal Voltage Gain	A <sub>VO</sub>	$V_S = \pm 15V, V_O = \pm 10V,$ $K_L = 2k\Omega$		50	200	_	V/mV
Supply Current	1	V _ +46V	PM-155		2	4	
Supply Current	l <sub>SY</sub>	V <sub>S</sub> = ±15V	PM-156/PM-157		5	7	mA
		A V	PM-155	_	5	_	
Slew Rate	SR	$A_{VCL} = +1, V_S = \pm 15V$	PM-156	7.5	12	_	V/μs
		$A_{VCL} = +5, V_S = \pm 15V$	PM-157	30	40		
		A - 14 V - 445V	PM-155	_	2.5	_	
Gain Bandwidth Product /	GBW	$A_{VCL} = +1, V_S = \pm 15V$	PM-156	_	5	_	MHz
	L ) )	A <sub>VCL</sub> = +5, V <sub>S</sub> = ± 15V	PM-157	_	20	_	
		V <sub>S</sub> = ±15V (Note 2)	PM-155	_	5	_	
Settling Time (to ±0.01%)	ts		PM-156	_	4	_	μ8
	$\bigcirc$	<b>V<sub>3</sub></b> = ± 15 <b>V</b> (Note 3)	PM-1577	_	4		
	$\overline{}$	$R_S = 100\Omega, f = 1000Hz$	)	_	25	_	
anut Naine Valtage	_ (	$R_S = 100\Omega$ , $f = 1000$ Hz	) PM-155	/ -~	20	7 =	-M/ /10-
nput Noise Voltage	e <sub>n</sub> `	$R_s = 100\Omega$ , $f = 100Hz$	PM-156/PM-157	·/ /`	15~	J	nV/√Hz
		$R_S = 100\Omega$ , $f = 1000Hz$	PM-130/PM-137	/ -	12	-	
		f = 100Hz, V <sub>S</sub> = ±15V				$\neg \neg$	
nput Noise Current	in	$f = 1000 Hz, V_S = \pm 15 V$		/-	0.04	-/	pAV√Hz
nput Capacitance	C <sub>IN</sub>				~3	_/	T OF
,	- 114			<del></del>	<del>- 1</del> -		<del></del>

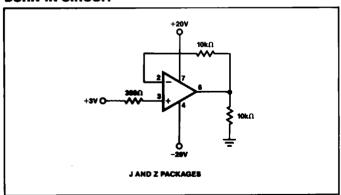
- current over the standard JFET input op amps.  $I_B$  and  $I_{OS}$  are measured at  $V_{CM} = 0$ .
- 2. Settling time is defined here for a unity gain inverter connection using  $2k\Omega$ resistors. It is the time required for the error voltage (the voltage at the inverting input pin on the amplifier) to settle to within 0.01% of its final value from the time a 10V step input is applied to the inverter. See settling time test circuit.
- 3. Settling time is defined here for a  $A_V$ =-5 connection with  $R_F$ =2k $\Omega$ . It is the time required for the error voltage (the voltage at the inverting input pin on the amplifier) to settle to within 0.01% of its final value from the time a 2V step input is applied to the inverter. See settling time test circuit.

### **BASIC CONNECTIONS**

### **SETTLING-TIME TEST CIRCUIT**



### **BURN-IN CIRCUIT**



### **APPLICATIONS INFORMATION**

### **INPUT VOLTAGE CONSIDERATIONS**

The PM series JFET input stages can accommodate large input differential voltages without external clamping as long as neither input exceeds the negative power supply. An input voltage which is more negative than V- can result in a destroyed unit.

If both inputs exceed the negative common-mode voltage limit, the amplifier will be forced to a high positive output. If only one input exceeds the negative common-mode voltage limit, a phase reversal takes place forcing the output to the corresponding high or low state. In either of the above conditions, normal operation will return when both inputs are returned to within the specified common-mode voltage range.

Exceeding the positive common-mode limit on a single input will not change the phase of the output. However, if both inputs exceed the limit, the output of the amplifier will be forced to a high state.

### **POWER SUPPLY CONSIDERATIONS**

Power supply polarity reversal can result in a destroyed unit.

### DYNAMIC OPERATING CONSIDERATIONS

As with most amplifiers, care should be taken with lead diess, component placement, and supply decoupling in order to ensure stability. For example, resistors from the output to an input should be placed with the body close to the input. This minimizes "pick-up" and increases the frequency of the feedback pole by minimizing the capacitance from input to ground.

A feedback pole is created when the feedback around any amplifier is resistive. The parallel resistance and capacitance from the input of the device to AC ground sets the frequency of the pole. In many instances, the frequency of this pole is much greater than the expected 3dB frequency of the closed-loop gain. Consequently, the pole has negligible effect on stability margin. However, if the feedback pole is less than approximately six times the expected 3dB frequency, a lead capacitor should be placed from the output to the inverting input of the op amp. The capacitor value should be such that the RC time constant of the capacitor and feedback resistor is greater than, or equal to, the original feedback-pole time constant.